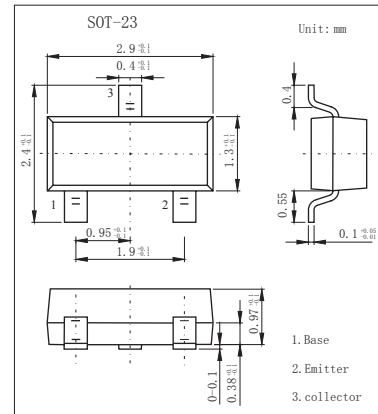


NPN Transistors

2SC1623



■ Features

- High DC Current Gain:
hFE = 200 TYP.
VCE = 6.0 V, IC = 1.0 mA
- High Voltage:
VCE O = 50 V

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	60	V
Collector to emitter voltage	V _{CEO}	50	V
Emitter to base voltage	V _{EBO}	5	V
Collector current (DC)	I _C	100	mA
Collector power dissipation	P _C	200	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CB0}	V _{CB} = 60V, I _E =0			0.1	μ A
Emitter cutoff current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	μ A
DC current gain *	h _{FE}	V _{CE} = 6V, I _C = 1mA	90	200	600	
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = 100mA, I _B = 10mA		0.15	0.3	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C = 100mA, I _B = 10mA		0.86	1	V
Base-emitter voltage *	V _{BE}	V _{CE} = 6V, I _C = 1mA	0.55	0.62	0.65	V
Output capacitance	C _{ob}	V _{CB} = 6V, I _E = 0, f = 1.0MHz		3.0		pF
Transiton Frequency	f _T	V _{CE} = 6V, I _E = -10mA		250		MHz

*. PW ≤ 350 us, duty cycle ≤ 2%

■ h_{FE} Classification

Marking	L4	L5	L6	L7
hFE	90 to 180	135 to 270	200 to 400	300 to 600



炬芯微
XUANXINWEI

SMD Type

Transistors

2SC1623

Typical Characteristics

